

Notice of References CitedApplication/Control No.
09/096,858Applicant(s)/Patent Under
Reexamination
NARWANKAR ET AL.Examiner
Anh D. MaiArt Unit
2814

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U.S. PATENT DOCUMENTS

*		Document Number	Date	Name	Classification	
		Country Code-Number-Kind Code	MM-YYYY			
	A	US-6,082,375-	07-2000	Gealy et al.	134	1.1
	B	US- -				
	C	US- -				
	D	US- -				
	E	US- -				
	F	US- -				
	G	US- -				
	H	US- -				
	I	US- -				
	J	US- -				
	K	US- -				
	L	US- -				
	M	US- -				

FOREIGN PATENT DOCUMENTS

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		Country Code-Number-Kind Code	MM-YYYY				
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	P	- -					
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	R	- -					
	S	- -					
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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Sun S. et al., Leakage Current Reduction in Chemical-Vapor-Deposited Ta2O5 Films by Rapid Thermal Annealing in N2O. 1996 IEEE, pp. 355-357.
	V	Wolf S. et al., Silicon Processing for the VLSI Era. 1986, Lattice Press Vol. 1, pp. 543-544 and 569-570.
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.